RX-0011



- Silicon PIN diode
- 120MHz bandwidth

Performance Highlights

- Typical responsivity 0.6A/W
- Operating temperature -40°C to +100°C
- Typical dark current 0.1nA

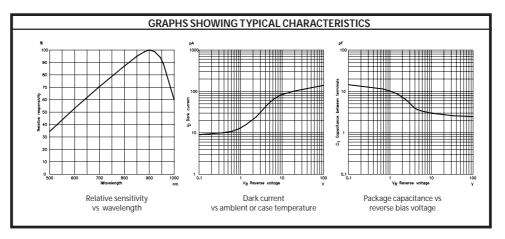
LIMITING VALUES	SYMBOL	VALUE	UNITS
Continuous reverse voltage	V _R	20	V
Operating temperature	T_{amb}	-40 to +100	°C
Storage temperature	T _{stg}	-40 to +125	°C
Soldering temperature 2mm from case for 10s (either device)	T_{sld}	260	°C

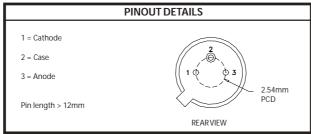
OPTICAL/ELECTRICAL CHARACTERISTICS	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITION
Responsivity (1)	R		0.6		A/W	$\lambda = 900$ nm, $V_R = 10$ V
Cutoff frequency	f _c		120		MHz	$R_L = 50\Omega$, $V_R = 10V$, $\lambda = 830$ nm
Peak sensitivity wavelength	$\lambda_{_{\mathrm{P}}}$		900			
Range of spectral sensitivity	Δλ	320		1060	nm	$S = 10\% \text{ of } S_{\text{max}}$
Active area			φ1.2		mm	
Capacitance	C _T		3		рF	$V_R = 10V, f = 1MHz$
Dark current	I _D		0.1	2	nA	$V_R = 10V$

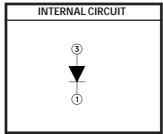
All values apply at a temperature of 25°C

(1) Responsivity data applies when used with fibres up to 62.5µm core diameter









NOTES:

1) The device is very susceptible to damage by electrostatic discharge.